



CASE T0-220B

THE TIP29 SERIES (NPN) AND TIP 30 SERIES (PNP) ARE COMPLEMENTARY SILICON EPITAXIAL BASE POWER TRANSISTORS DESIGNED FOR POWER AMPLIFIERS AND SWITCHING APPLICATIONS.



BCE

ABSOLUTE MAXIMUM RATINGS For p-n-p devices, voltage and current values are negative.

| | | | | | |
|---|----------|--------------|------|-----|------|
| Collector-Base Voltage | VCBO | 40V | 60V | 80V | 100V |
| Collector-Emitter Voltage | VCEO | 40V | 60V | 80V | 100V |
| Emitter-Base Voltage | VEBO | 5V | 5V | 5V | 5V |
| Collector Current | IC | 1A | 1A | 1A | 1A |
| Collector Peak Current | ICM | 3A | 3A | 3A | 3A |
| Base Current | IB | | 0.4A | | |
| Total Power Dissipation @ $T_G \leq 25^\circ\text{C}$ | Ptot | | 30W | | |
| @ $T_A \leq 25^\circ\text{C}$ | | | 2W | | |
| Operating Junction & Storage Temperature | Tj, Tstg | -65 to 150°C | | | |

| | | | |
|-------|--------|--------|--------|
| TIP29 | TIP29A | TIP29B | TIP29C |
| TIP30 | TIP30A | TIP30B | TIP30C |

THERMAL RESISTANCE

| | | | |
|---------------------|---------------|----------|------|
| Junction to Case | θ_{jc} | 4.17°C/W | max. |
| Junction to Ambient | θ_{ja} | 62.5°C/W | max. |

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

| PARAMETER | SYMBOL | TIP29 | | TIP29A | | TIP29B | | UNIT | TEST CONDITIONS |
|--------------------------------------|-----------|-------|-----|--------|--------|--------|-----|------|---------------------------|
| | | TIP30 | MIN | MAX | TIP30A | MIN | MAX | | |
| Collector-Emitter Breakdown Voltage | LVCEO* | 40 | | 60 | | 80 | | V | IC=30mA IB=0 |
| Collector Cutoff Current | ICEO | 0.3 | | 0.3 | | 0.3 | | mA | VCE=30V IB=0 |
| | | | | | | | | mA | VCE=60V IB=0 |
| Collector Cutoff Current | ICES | 0.2 | | 0.2 | | 0.2 | | mA | VCE=40V VBE=0 |
| | | | | | | | | mA | VCE=60V VBE=0 |
| | | | | | | | | mA | VCE=80V VBE=0 |
| Emitter Cutoff Current | IEBO | 1 | | 1 | | 1 | | mA | VEB=5V IC=0 |
| Collector-Emitter Saturation Voltage | VCE(sat)* | 0.7 | | 0.7 | | 0.7 | | V | IC=1A IB=125mA |
| Base-Emitter Voltage | VBE * | 1.3 | | 1.3 | | 1.3 | | V | IC=1A VCE=4V |
| D.C. Current Gain | HFE | 40 | | 40 | | 40 | | | IC=0.2A VCE=4V |
| | | 15 | 75 | 15 | 75 | 15 | 75 | | IC=1A VCE=4V |
| Small Signal Current Gain | hfe | 20 | | 20 | | 20 | | | IC=0.2A VCE=10V f=1kHz |
| Current Gain-Bandwidth Product | fT | 3 | | 3 | | 3 | | MHz | IC=0.2A VCE=10V f=1MHz |

* Pulse Test : Pulse Width=0.3mS, Duty Cycle=1%

TIP30C same as TIP30B, except LVCEO.

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1-1. B-P

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